

IN THE SPECIFICATION

Please replace the paragraph on page 3, lines 11-17 with the following rewritten paragraph:

A depth D1 of the first diffusion layer from the first side of the semiconductor substrate and a depth D2 of the second diffusion layer from the second side of the semiconductor substrate may have a relation of $D1 > D2$. The depth D2 of the second diffusion layer and a depth D3 of the third diffusion layer from the second side of the semiconductor substrate may have a relation of $D2 > D3$. The depth D1 of the first diffusion layer, the depth D2 of the second diffusion layer and the depth D3 of the third diffusion layer may have a relation of $D1 > D2 > D3$.

Please replace the paragraph on page 9, lines 16-23 with the following rewritten paragraph:

Especially, the depth D2 of the second diffusion layer 12 from the second side of the semiconductor substrate is preferably smaller than a depth D1 of the first diffusion layer 11 from the first side of the semiconductor substrate, whereby the reverse recovery characteristics and the reverse-blocking withstand voltage characteristic can be more improved. The depth D1 of the first diffusion layer 11 and the depth D2 of the second diffusion layer 12, are respectively selected, for example, within a range of 50 to 100 μm and in a relation of $D1 > D2$.

Please replace the paragraph from page 13, line 21 to page 14, line 5 with the following rewritten paragraph:

Especially, the depth D3 of the third diffusion layer 13 from the second side of the semiconductor substrate is preferably smaller than a depth D1 of the first diffusion layer 11

from the first side of the semiconductor substrate and the depth D2 of the second diffusion layer 12 from the second side of the semiconductor substrate, whereby the reverse recovery characteristics and the reverse-blocking withstand voltage characteristic can be more improved. The depth D1 of the first diffusion layer 11, the depth D2 of the second diffusion layer 12 and the depth D3 of the third diffusion layer 13 are respectively selected, for example, within a range of 50 to 100 μm , and in a relation of $D1 > D2 > D3$.

Please replace the paragraph from page 16, line 18 to page 17, line 2 with the following rewritten paragraph:

Especially, the depth D3 of the third diffusion layer 13 from the second side of the semiconductor substrate is preferably smaller than a depth D1 of the first diffusion layer 11 from the first side of the semiconductor substrate and the depth D2 of the second diffusion layer 12 from the second side of the semiconductor substrate, whereby the reverse recovery characteristics and the reverse-blocking withstand voltage characteristic can be more improved. The depth D1 of the first diffusion layer 11, the depth D2 of the second diffusion layer 12 and the depth D3 of the third diffusion layer 13 are respectively selected, for example, within a range of 50 to 100 μm , and in a relation of $D1 > D2 > D3$.

Please replace the paragraph on page 22, lines 4-13 with the following rewritten paragraph:

Especially, the depth D3 of the third diffusion layer 13 from the second side of the semiconductor substrate is preferably smaller than a depth D1 of the first diffusion layer 11 from the first side of the semiconductor substrate and the depth D2 of the second diffusion layer 12 from the second side of the semiconductor substrate, whereby the reverse recovery characteristics and the reverse-blocking withstand voltage characteristic can be more

improved. The depth D1 of the first diffusion layer 11, the depth D2 of the second diffusion layer 12 and the depth D3 of the third diffusion layer 13 are respectively selected, for example, within a range of 50 to 100 μm , and in a relation of $D1 > D2 > D3$.

Please replace the paragraph on page 26, lines 4-13 with the following rewritten paragraph:

Especially, the depth D3 of the third diffusion layer 13 from the second side of the semiconductor substrate is preferably smaller than a depth D1 of the first diffusion layer 11 from the first side of the semiconductor substrate and the depth D2 of the second diffusion layer 12 from the second side of the semiconductor substrate, whereby the reverse recovery characteristics and the reverse-blocking withstand voltage characteristic can be more improved. The depth D1 of the first diffusion layer 11, the depth D2 of the second diffusion layer 12 and the depth D3 of the third diffusion layer 13 are respectively selected, for example, within a range of 50 to 100 μm , and in a relation of $D1 > D2 > D3$.